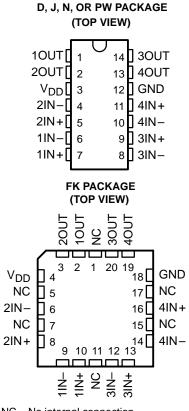
- Single- or Dual-Supply Operation
- Wide Range of Supply Voltages 2 V to 18 V
- Very Low Supply Current Drain 0.3 mA Typ at 5 V
- Fast Response Time . . . 200 ns Typ for TTL-Level Input Step
- Built-In ESD Protection
- High Input Impedance . . . $10^{12} \Omega$ Typ
- Extremely Low Input Bias Current 5 pA Typ
- Ultrastable Low Input Offset Voltage
- Input Offset Voltage Change at Worst-Case Input Conditions Typically 0.23 μV/Month, Including the First 30 Days
- Common-Mode Input Voltage Range Includes Ground
- Outputs Compatible With TTL, MOS, and CMOS
- Pin-Compatible With LM339

description

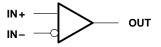
These quadruple differential comparators are fabricated using LinCMOSTM technology and consist of four independent voltage comparators designed to operate from a single power supply. Operation from dual supplies is also possible if the difference between the two supplies is 2 V to 18 V. Each device features extremely high input impedance (typically greater than $10^{12} \Omega$), allowing direct interfacing with high-impedance sources. The outputs are n-channel open-drain configurations and can be connected to achieve positive-logic wired-AND relationships.



SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

NC - No internal connection

symbol (each comparator)



The TLC374 has internal electrostatic discharge (ESD) protection circuits and has been classified with a 1000-V ESD rating using human body model testing. However, care should be exercised in handling this device as exposure to ESD may result in degradation of the device parametric performance.

The TLC374C is characterized for operation from 0°C to 70°C. The TLC374I is characterized for operation from -40° to 85° C. The TLC374M is characterized for operation over full military temperature range of -55° C to 125° C. The TLC374Q is characterized for operation from -40° C to 125° C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

LinCMOS is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



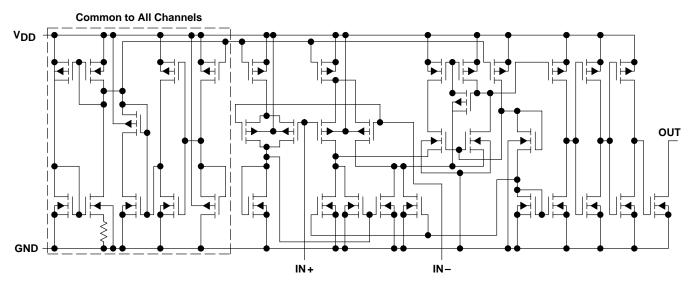
Copyright © 1999, Texas Instruments Incorporated

SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

AVAILABLE OPTIONS												
		PACKAGED DEVICES										
Т _А	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	FORM (Y)					
0°C to 70°C	5 mV	TLC374CD			TLC374CN	TLC374CPW	TLC374Y					
-40°C to 85°C	5 mV	TLC374ID			TLC374IN		—					
-55°C to 125°C	5 mV	TLC374MD	TLC374MFK	TLC374MJ	TLC374MN	_	_					
-40°C to 125°C	5 mV	TLC374QD		_	TLC374QN		—					

The D packages are available taped and reeled. Add R suffix to device type (e.g., TLC374CDR).

equivalent schematic (each comparator)

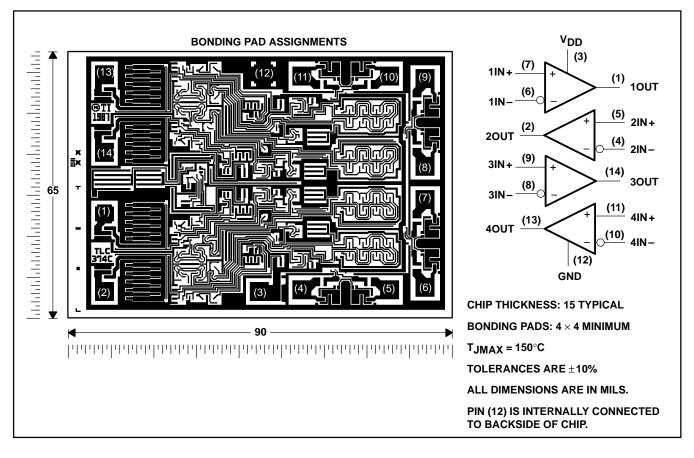




SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

TLC374Y chip information

This chip, when properly assembled, displays characteristics similar to the TLC374C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.





SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

18 V 18 V
V _{DD}
18 V
18 V
5 mA
0 mA
mited
Table
70°C
85°C
25°C
25°C
50°C
260°C
260°C
00°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values except differential voltages are with respect to network ground.

2. Differential voltages are at IN+ with respect to IN –.

3. Short circuits from outputs to V_{DD} can cause excessive heating and eventual device destruction.

		DIS	SIPATION RAT	ING TABLE		
PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	500 mW	7.6 mW/°C	84°C	500 mW	494 mW	190 mW
FK	500 mW	11.0 mW/°C	104°C	500 mW	500 mW	269 mW
J	500 mW	11.0 mW/°C	104°C	500 mW	500 mW	269 mW
Ν	500 mW	9.2 mW/°C	95°C	500 mW	500 mW	224 mW
PW	700 mW	5.6 mW/°C	—	448 mW	—	—

recommended operating conditions

		TLC3	874C	TLC	374I	TLC3	374M	TLC3	374Q	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	3	16	4	16	3	16	V
Common-mode input voltage, VIC	$V_{DD} = 5 V$	0	3.5	0	3.5	0	3.5	0	3.5	V
Common-mode input voitage, v[C	V _{DD} = 10 V	0	8.5	0	8.5	0	8.5	0	8.5	v
Operating free-air temperature, TA		0	70	-40	85	-55	125	-40	125	°C



	10	I
	IВ	I
	VICR	(
POST (ЮН	ł
	VOL	L
	lol	L
	DD	(
TEXAS INSTRUMENTS POST OFFICE BOX 655303* DALLAS, TEXAS 75265	All cha 125°C Paran IOTE 4	c fo

				_ +	TLC	C374C		TLC	C374I		TLC	374M		
Î	PARAMETER	TEST CONI	DITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	Input offect veltage	V _{IC} = V _{ICR} min, See Note 4		25°C		1	5		1	5		1	5	mV
VIO	Input offset voltage	VIC = VICRIMIN,	See Note 4	Full range			6.5			7			10	mv
10	Input offset current			25°C		1			1			1		pА
10	input onset current			MAX			0.3			1			10	nA
lun.	Input bias current			25°C		5			5			5		pА
lΒ	Input bias current			MAX			0.6			2			20	nA
Common-mode input				25°C	0 to V _{DD} −1			0 to V _{DD} -1			0 to V _{DD} -1			V
VICR	voltage range			Full range	0 to V _{DD} -1.5			0 to V _{DD} -1.5			0 to V _{DD} -1.5			v
lau	High-level output current	V _{ID} = 1 V	V _{OH} = 5 V	25°C		0.1			0.1			0.1		nA
ЮН	riigii-level output current	VID = 1 V	V _{OH} = 15 V	Full range			1			1			1	μΑ
Vei	Low-level output voltage			25°C		150	400		150	400		150	400	mV
VOL	Low-level output voltage	V _{ID} = -1 V,	$I_{OL} = 4 \text{ mA}$	Full range			700			700			700	mv
IOL	Low-level output current	$V_{ID} = -1 V$,	V _{OL} = 1.5 V	25°C	6	16		6	16		6	16		mA
	Supply current		No load	25°C		300	600		300	600		300	600	
^I DD	(four comparators)	V _{ID} = 1 V,	INU IUdu	Full range			800			800			800	μA

racteristics are measured with zero common-mode input voltage unless otherwise noted. Full range is 0°C to 70°C for TLC374C, -40°C to 85°C for TLC374I, and -55°C to for the TLC374M, and -40°C to 125°C for TLC374Q. IMPORTANT: See eter Measurement Information.

The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, $V_{DD} = 5 V$, $T_A = 25^{\circ}C$

PARAMETER	TEST C	TEST CONDITIONS					
	MIN	MIN TYP MAX					
Perpanan time	R_L connected to 5 V through 5.1 k Ω ,	100-mV input step with 5-mV overdrive		650		20	
Response time	$C_L = 15 \text{ pF}^{\ddagger}$, See Note 5	TTL-level input step	200		ns		

[‡]C_L includes probe and jig capacitance. NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses 1.4 V.

SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

electrical characteristics at specified free-air temperature, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEST CON	DITIONS	TLC			
	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	
VIO	Input offset voltage	$V_{IC} = V_{ICR}min,$	See Note 4		1	5	mV
IIO	Input offset current				1		pА
IIB	Input bias current				5		pА
VICR	Common-mode input voltage range			0 to V _{DD} -1			V
IОН	High-level output current	V _{ID} = 1 V,	V _{OH} = 5 V		0.1		nA
VOL	Low-level output voltage	$V_{ID} = -1 V$,	I _{OL} = 4 mA		150	400	mV
IOL	Low-level output current	$V_{ID} = -1 V$,	V _{OL} = 1.5 mV	6	16		mA
IDD	Supply current (four comparators)	V _{ID} =1 V,	No load		300	600	μΑ

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, V_{DD} = 5 V, T_A = 25°C

PARAMETER	TEST	Т	UNIT			
PARAMETER TEST CONDITIONS MIN						UNIT
Beenenge time	R_L connected to 5 V through 5.1 k Ω ,	100-mV input step with 5-mV overdrive		650		
Response time	$C_L = 15 \text{ pF}^{\dagger}$, See Note 5	TTL-level input step		200		ns

[†]C_L includes probe and jig capacitance.

NOTE 4: The response time specified is the interval between the input step function and the instant when the output crosses 1.4 V.



SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

PARAMETER MEASUREMENT INFORMATION

The digital output stage of the TLC374 can be damaged if it is held in the linear region of the transfer curve. Conventional operational amplifier/comparator testing incorporates the use of a servo loop that is designed to force the device output to a level within this linear region. Since the servo-loop method of testing cannot be used, the following alternative for measuring parameters such as input offset voltage, common-mode rejection, etc., are offered.

To verify that the input offset voltage falls within the limits specified, the limit value is applied to the input as shown in Figure 1(a). With the noninverting input positive with respect to the inverting input, the output should be high. With the input polarity reversed, the output should be low.

A similar test can be made to verify the input offset voltage at the common-mode extremes. The supply voltages can be slewed as shown in Figure 1(b) for the V_{ICR} test, rather than changing the input voltages, to provide greater accuracy.

A close approximation of the input offset voltage can be obtained by using a binary search method to vary the differential input voltage while monitoring the output state. When the applied input voltage differential is equal, but opposite in polarity to the input offset voltage, the output changes state.

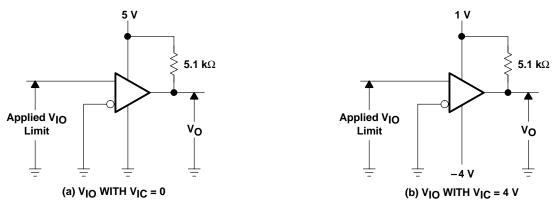


Figure 1. Method for Verifying That Input Offset Voltage is Within Specified Limits



SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

PARAMETER MEASUREMENT INFORMATION

Figure 2 illustrates a practical circuit for direct dc measurement of input offset voltage that does not bias the comparator into the linear region. The circuit consists of a switching-mode servo loop in which U1a generates a triangular waveform of approximately 20-mV amplitude. U1b acts as a buffer with C2 and R4 removing any residual dc offset. The signal is then applied to the inverting input of the comparator under test, while the noninverting input is driven by the output of the integrator formed by U1c through the voltage divider formed by R9 and R10. The loop reaches a stable operating point when the output of the comparator under test has a duty cycle of exactly 50%, which can only occur when the incoming triangle wave is sliced symmetrically or when the voltage at the noninverting input exactly equals the input offset voltage.

Voltage divider R9 and R10 provide a step up of the input offset voltage by a factor of 100 to make measurement easier. The values of R5, R8, R9, and R10 can significantly influence the accuracy of the reading; therefore, it is suggested that their tolerance level be 1% or lower.

Measuring the extremely low values of input current requires isolation from all other sources of leakage current and compensation for the leakage of the test socket and board. With a good picoammeter, the socket and board leakage can be measured with no device in the socket. Subsequently, this open-socket leakage value can be subtracted from the measurement obtained with a device in the socket to obtain the actual input current of the device.

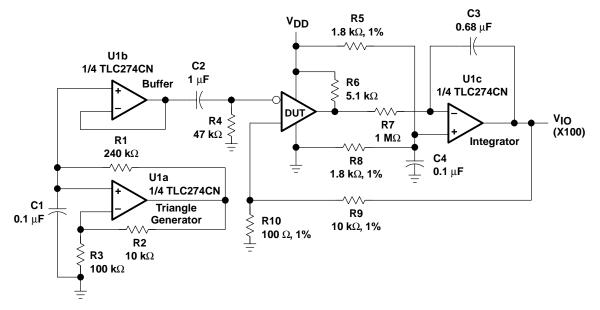


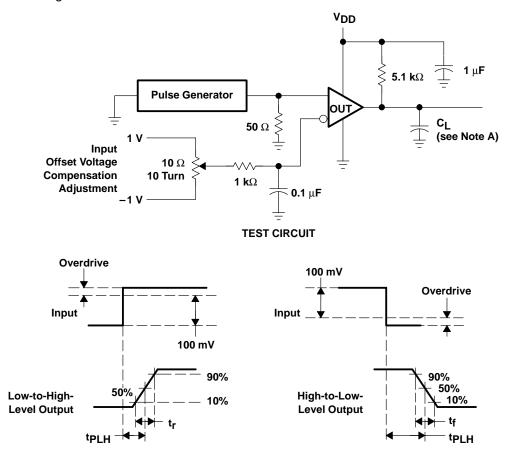
Figure 2. Test Circuit for Input Offset Voltage Measurement



SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

PARAMETER MEASUREMENT INFORMATION

Response time is defined as the interval between the application of an input step function and the instant when the output reaches 50% of its maximum value. Response time, low-to-high-level output, is measured from the trailing edge of the input pulse. Response-time measurement at low input signal levels can be greatly affected by the input offset voltage. The offset voltage should be balanced by the adjustment at the inverting input (as shown in Figure 3) so that the circuit is just at the transition point. Then a low signal, for example, 105-mV or 5-mV overdrive, causes the output to change state.



VOLTAGE WAVEFORMS

NOTE A: CL includes probe and jig capacitance.





SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

PRINCIPLES OF OPERATION

LinCMOS process

LinCMOS process is a linear polysilicon-gate complimentary-MOS process. Primarily designed for singlesupply applications, LinCMOS products facilitate the design of a wide range of high-performance analog functions from operational amplifiers to complex mixed-mode converters.

While digital designers are experienced with CMOS, MOS technologies are relatively new for analog designers. This short guide is intended to answer the most frequently asked questions related to the quality and reliability of LinCMOS products. Further questions should be directed to the nearest TI field sales office.

electrostatic discharge

CMOS circuits are prone to gate oxide breakdown when exposed to high voltages even if the exposure is only for very short periods of time. Electrostatic discharge (ESD) is one of the most common causes of damage to CMOS devices. It can occur when a device is handled without proper consideration for environmental electrostatic charges, e.g. during board assembly. If a circuit in which one amplifier from a dual operational amplifier is being used and the unused pins are left open, high voltages tends to develop. If there is no provision for ESD protection, these voltages may eventually punch through the gate oxide and cause the device to fail. To prevent voltage buildup, each pin is protected by internal circuitry.

Standard ESD-protection circuits safely shunt the ESD current by providing a mechanism whereby one or more transistors break down at voltages higher than normal operating voltages but lower than the breakdown voltage of the input gate. This type of protection scheme is limited by leakage currents which flow through the shunting transistors during normal operation after an ESD voltage has occurred. Although these currents are small, on the order of tens of nanoamps, CMOS amplifiers are often specified to draw input currents as low as tens of picoamps.

To overcome this limitation, TI design engineers developed the patented ESD-protection circuit shown in Figure 4. This circuit can withstand several successive 1-kV ESD pulses, while reducing or eliminating leakage currents that may be drawn through the input pins. A more detailed discussion of the operation of TI's ESD-protection circuit is presented on the next page.

All input an output pins of LinCMOS and Advanced LinCMOS products have associated ESD-protection circuitry that undergoes qualification testing to withstand 1000 V discharged from a 100-pF capacitor through a 1500- Ω resistor (human body model) and 200 V from a 100-pF capacitor with no current-limiting resistor (charged device model). These tests simulate both operator and machine handling of devices during normal test and assembly operations.

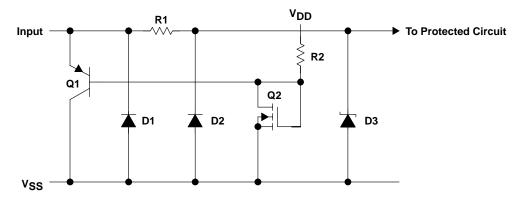


Figure 4. LinCMOS ESD-Protection Schematic



PRINCIPLES OF OPERATION

Input protection circuit operation

Texas Instruments patented protection circuitry allows for both positive- and negative-going ESD transients. These transients are characterized by extremely fast rise times and usually low energies, and can occur both when the device has all pins open and when it is installed in a circuit.

positive ESD transients

Initial positive charged energy is shunted through Q1 to V_{SS}. Q1 turns on when the voltage at the input rises above the voltage on V_{DD} by a value equal to the V_{EB} of Q1. The base current increases through R2 with input current as Q1 saturates. The base current through R2 as Q1 saturates forces the voltage at the drain and gate of Q2 to exceed its threshold level (V_T ~ 22 to 26 V) and turn on Q2. The shunted input current through Q1 to V_{SS} is now shunted through the n-channel enhancement-type MOSFET Q2 to V_{SS}. If the voltage on the input pin continues to rise, the breakdown voltage of d3 is exceeded and all remaining energy is dissipated in R1 and D3. The breakdown voltage of D3 is designed to be 24 V to 27 V, which is well below the gate oxide voltage of the circuit to be protected.

negative ESD transients

The negative charged ESD transients are shunted directly through D1. Additional energy is dissipated in R1 and D2 as D2 becomes forward-biased. The voltage seen by the protected circuit is -0.3 V to -1 V (the forward voltage of D1 and D2).

circuit-design considerations

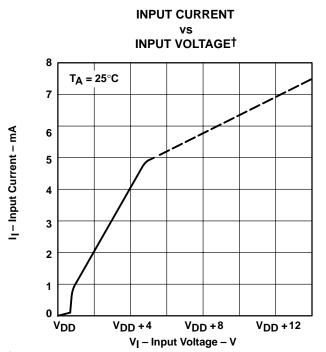
LinCMOS products are being used in actual circuits environments that have input voltages that exceed the recommended common-mode input voltage range and activate the input protection circuit. Even under normal operation, these conditions occur during circuit power up or power down, and in many cases, when the device is being used for a signal conditioning function. The input voltages can exceed V_{ICR} and not damage the device only if the inputs are current limited. The recommended current limit shown on most product data sheets is ± 5 mA. Figures 5 and 6 show typical characteristics for input voltage vs input current.

Normal operation and correct output state can be expected even when the input voltage exceeds the positive supply voltage. The input current should be externally limited even through internal positive current limiting is achieved in the input protection circuit by the action of Q1. When Q1 is on, it saturates and limits the current to approximately 5-mA collector current by design. When saturated, Q1 base current increases with input current. This current is forced into the V_{DD} pin and into the device I_{DD} or the V_{DD} supply through R2 producing the current limiting effects shown in Figure 5. This internal limiting lasts only as long as the input voltage is below the V_T of Q2.

When the input voltage exceeds the negative supply voltage, normal operation is affected and output voltage states may not be correct. Also, the isolation between channels of multiple devices (duals and quads) can be severely affected. External current limiting must be used since this current is directly shunted by D1 and D2, and no internal limiting is achieved. If normal output voltage states are required, an external input voltage clamp is required (see Figure 7).



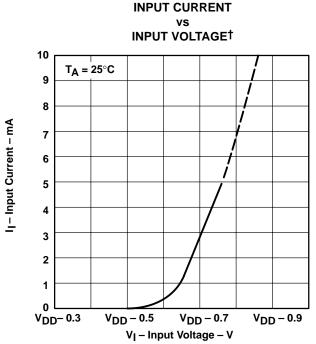
SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999



PRINCIPLES OF OPERATION

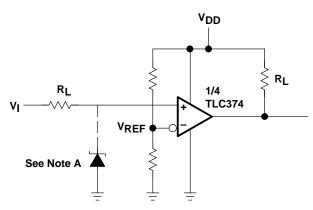
[†]The dashed line identifies an area of operation where some degradation of parametric performance may be experienced.

Figure 5



[†]The dashed line identifies an area of operation where some degradation of parametric performance may be experienced.

Figure 6



Positive Voltage Input Current Limit: $R_{I} = \frac{+V_{I} - V_{DD} - 0.3 V}{5 \text{ mA}}$ Negative Voltage Input Current Limit: $R_{I} = \frac{-V_{I} - V_{DD} - (0.3 V)}{5 \text{ mA}}$

NOTE A: If the correct output state is required when the negative input exceeds VSS, a Schotty clamp is required.

Figure 7. Typical Input Current-Limiting Configuration for a LinCMOS Comparator





10-Jun-2014

PACKAGING INFORMATION

Orderable Device		Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
5962-87659012A	(1) ACTIVE	LCCC	FK	20	1	(2) TBD	(6) POST-PLATE	⁽³⁾ N / A for Pkg Type	-55 to 125	(4/5) 5962- 87659012A TLC374MFKB	Samples
5962-8765901CA	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-8765901CA TLC374MJB	Samples
TLC374CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC374C	Samples
TLC374CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC374C	Samples
TLC374CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC374C	Samples
TLC374CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC374C	Samples
TLC374CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC374CN	Samples
TLC374CN-A	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC374CN_A	Samples
TLC374CNE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC374CN	Samples
TLC374CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC374	Samples
TLC374CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P374	Samples
TLC374CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P374	Samples
TLC374CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	0 to 70		
TLC374CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P374	Samples
TLC374CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P374	Samples
TLC374ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC374I	Samples
TLC374IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC374I	Samples



10-Jun-2014

Orderable Device	Status	Package Type		Pins	-	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLC374IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC374I	Samples
TLC374IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC374I	Samples
TLC374IN	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC374IN	Samples
TLC374INE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC374IN	Samples
TLC374MD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	TLC374M	Samples
TLC374MDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		TLC374M	Samples
TLC374MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	5962- 87659012A TLC374MFKB	Samples
TLC374MJ	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	TLC374MJ	Samples
TLC374MJB	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-8765901CA TLC374MJB	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



www.ti.com

10-Jun-2014

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLC374, TLC374M :

- Catalog: TLC374
- Military: TLC374M

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

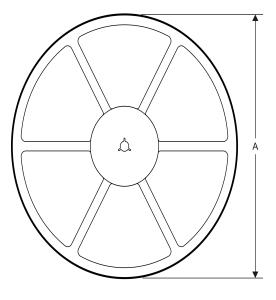
PACKAGE MATERIALS INFORMATION

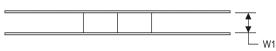
www.ti.com

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE AND REEL INFORMATION

TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC374CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC374CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC374CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC374IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

14-Jul-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC374CDR	SOIC	D	14	2500	333.2	345.9	28.6
TLC374CNSR	SO	NS	14	2000	367.0	367.0	38.0
TLC374CPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
TLC374IDR	SOIC	D	14	2500	367.0	367.0	38.0

J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

LEADLESS CERAMIC CHIP CARRIER

FK (S-CQCC-N**) 28 TERMINAL SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



A. An integration of the information o

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE

0,51 0,35 ⊕0,25⊛ 1,27 8 14 0,15 NOM 5,60 8,20 5,00 7,40 \bigcirc Gage Plane ₽ 0,25 7 1 1,05 0,55 0°-10° Δ 0,15 0,05 Seating Plane — 2,00 MAX 0,10PINS ** 14 16 20 24 DIM 10,50 10,50 12,90 15,30 A MAX A MIN 9,90 9,90 12,30 14,70 4040062/C 03/03

NOTES: A. All linear dimensions are in millimeters.

NS (R-PDSO-G**)

14-PINS SHOWN

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications				
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive			
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications			
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers			
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps			
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy			
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial			
Interface	interface.ti.com	Medical	www.ti.com/medical			
Logic	logic.ti.com	Security	www.ti.com/security			
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense			
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video			
RFID	www.ti-rfid.com					
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com			
Wireless Connectivity	www.ti.com/wirelessconnectivity					

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2015, Texas Instruments Incorporated